



Table 6.1

Parameter Symbol	Parameter Description	Typical Parameter Value		Units
		n-Channel	p-Channel	
V_{T0}	Threshold voltage ($V_{BS} = 0$)	0.7 ± 0.15	-0.7 ± 0.15	V
K'	Transconductance parameter (in saturation)	$110.0 \pm 10\%$	$50.0 \pm 10\%$	$\mu\text{A}/\text{V}^2$
γ	Bulk threshold parameter	0.4	0.57	$\text{V}^{1/2}$
λ	Channel length modulation parameter	$0.04 (L = 1 \mu\text{m})$ $0.01 (L = 2 \mu\text{m})$	$0.05 (L = 1 \mu\text{m})$ $0.01 (L = 2 \mu\text{m})$	V^{-1}
$2 \phi_F $	Surface potential at strong inversion	0.7	0.8	V

6.1 Determine V_{ref} (Output Voltage) in Fig 6.1 and the conditions under which the TC of V_{ref} is zero. Assume $K=10$. Assume $(\partial V_T)/\partial T=0.085\text{mV}/^\circ\text{C}$, $(\partial V_{BE})/\partial T=-2\text{mV}/^\circ\text{C}$, $V_{BE}=0.75\text{V}$, $V_T=26\text{mV}$.

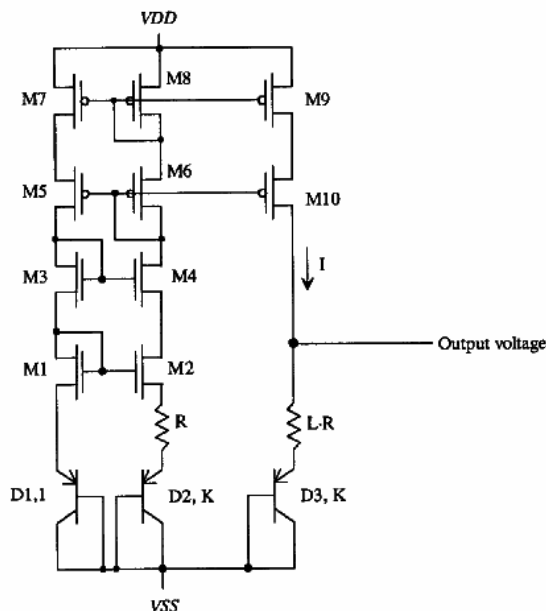


Fig 6.1

解:

For the circuit in Fig 6.1, we get

$$V_{\text{ref}} = L \ln K \times V_T + V_{BE(D3)}.$$

V_{ref} is dependent on temperature and we get

$$\frac{\partial V_{\text{ref}}}{\partial T} = L \cdot \ln K \cdot \frac{\partial V_T}{\partial T} + \frac{\partial V_{d3}}{\partial T}$$

$$\frac{\partial V_T}{\partial T} = 0.085\text{mV}/^\circ\text{C} \quad \text{and} \quad \frac{\partial V_{d3}}{\partial T} = -2\text{mV}/^\circ\text{C}$$

Let V_{ref} has zero temperature coefficient and get

$$\frac{\partial V_{\text{ref}}}{\partial T} = L \cdot \ln K \cdot \frac{\partial V_T}{\partial T} + \frac{\partial V_{d3}}{\partial T} = 0$$

It can be derived that while $L \cdot \ln K = 2/0.085 = 23.5$, $\frac{\partial V_{ref}}{\partial T} = 0$, or $TC(V_{ref}) = 0$.

Assuming $K=10$, the corresponding $L=10.2 \approx 10$

Under these conditions the V_{ref} that has zero TC is

$$V_{REF} = L \ln K \times V_T + V_{BE(D3)} = 1.35V$$

6.2 Derive an expression for I_{out} in Fig 6.2. Assume all transistors are in saturation region, and $(W/L)_4 = (W/L)_3$, $\lambda=0$.

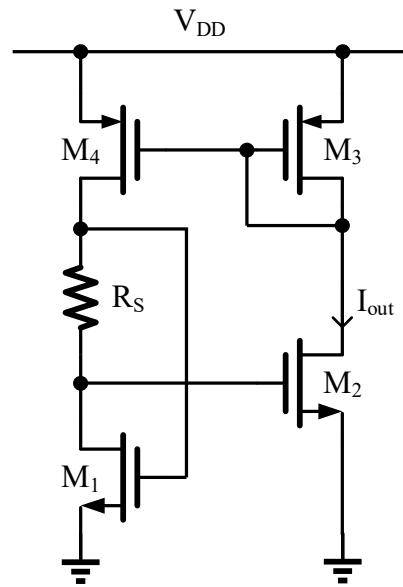


Fig 6.2

解:

$$I_{out} R_S + \sqrt{\frac{2I_{out}}{\mu_n C_{ox} \left(\frac{W}{L}\right)_2}} + V_{TH2} = \sqrt{\frac{2I_{out}}{\mu_n C_{ox} \left(\frac{W}{L}\right)_1}} + V_{TH1}$$

$$\text{解得: } I_{out} = \frac{2}{\mu_n C_{ox} R_S^2} \left(\sqrt{\left(\frac{L}{W}\right)_1} - \sqrt{\left(\frac{L}{W}\right)_2} \right)^2$$

Homework for this week is a few choice questions.

6.3 A current mirror circuit is shown in Fig 6.3. In order to make I_o strictly equals to I_{ref} , what is the expression of V_b ? $\lambda=0$. ()

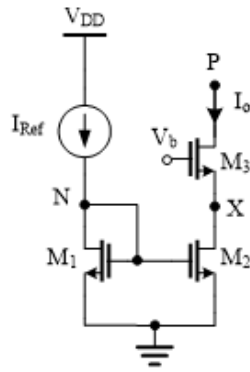


Fig 6.3

- A. $2V_{OD} + 2V_{th}$
- B. $2V_{OD} + 2V_{GS}$
- C. $2V_{OD} + V_{th}$
- D. $2V_{OD}$

Answer: A or C

6.4 In Fig 6.3, what is the minimum value of I_0 ? $\lambda=0$. ()

- A. $2V_{OD} + 2V_{th}$
- B. $2V_{OD} + 2V_{GS}$
- C. $2V_{OD} + V_{th}$
- D. $2V_{OD}$

Answer: D

6.5 How many current mirror circuit blocks exist in Fig 6.4? ()

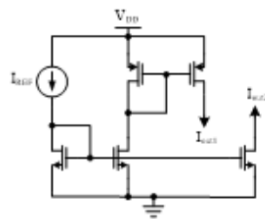


Fig 6.4

- A. 1
- B. 2
- C. 3
- D. 4

Answer: C

6.6 Assume you are an analog IC designer. When you are designing a current mirror, what device parameter should be the same to reduce mismatch? ()

- A. W
- B. L
- C. W/L

Answer: B